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Data Sheet December 10, 2015 FN9220.4

Dual LDO with Low Noise, Low I_Q , and High PSRR

ISL9012 is a high performance dual LDO capable of sourcing 150mA current from Channel 1, and 300mA from Channel 2. The device has a low standby current and high-PSRR and is stable with output capacitance of $1\mu F$ to $10\mu F$ with ESR of up to $200m\Omega$.

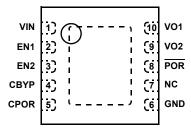
The device integrates a Power-On-Reset (POR) function for the VO2 output. The POR delay for VO2 can be externally programmed by connecting a timing capacitor to the CPOR pin. A reference bypass pin is also provided for connecting a noise-filtering capacitor for low noise and high PSRR applications.

The quiescent current is typically only 45µA with both LDO's enabled and active. Separate enable pins control each individual LDO output. When both enable pins are low, the device is in shutdown, typically drawing less than 0.1µA.

Several combinations of voltage outputs are standard. Output voltage options for each LDO range from 1.5V to 3.3V. Other output voltage options are available on request.

Pinout

ISL9012 (10 LD 3X3 DFN) TOP VIEW



Features

- · Integrates two high performance LDOs
 - VO1 150mA output
 - VO2 300mA output
- Excellent transient response to large current steps
- Excellent load regulation:
 1% voltage change across full range of load current
- High PSRR: 70dB @ 1kHz
- · Wide input voltage capability: 2.3V to 6.5V
- Extremely low quiescent current: 45µA (both LDOs on)
- · Low dropout voltage: typically 120mV @ 150mA
- Low output noise: typically 30μV_{RMS} @ 100μA (1.5V)
- Stable with 1 to10µF ceramic capacitors
- · Separate enable pins for each LDO
- POR output, with adjustable delay time indicates when the VO2 output is good
- · Soft-start to limit input current surge during enable
- · Current limit and overheat protection
- ±1.8% accuracy over all operating conditions
- Tiny 10 Ld 3x3mm DFN package
- -40°C to +85°C operating temperature range
- · Pin compatible with Micrel MIC2212
- · Pb-free (RoHS compliant)

Applications

- · PDAs, Cell Phones and Smart Phones
- · Portable Instruments, MP3 Players
- · Handheld Devices including Medical Handhelds

Ordering Information

PART NUMBER (Notes 1, 2, 3)	PART MARKING	VO1 VOLTAGE (V)	VO2 VOLTAGE (V)	TEMP RANGE (°C)	PACKAGE (Pb-free)	PKG. DWG. #
ISL9012IRNNZ	DCTA	3.3	3.3	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
ISL9012IRNJZ (No longer available, recommended replacement: ISL9000AIRNJZ)	DAPA	3.3	2.8	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
SL9012IRNFZ (No longer available, recommended replacement: ISL9000AIRNFZ)	DARA	3.3	2.5	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
ISL9012IRMNZ	DCYA	3.0	3.3	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
ISL9012IRMMZ (No longer available, recommended replacement: ISL9000AIRMGZ-T)	DAAK	3.0	3.0	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
ISL9012IRMGZ	DCBC	3.0	2.7	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
ISL9012IRJNZ	DCBD	2.8	3.3	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
ISL9012IRJMZ (No longer available, recommended replacement: ISL9000AIRJBZ-T)	DAAH	2.8	3.0	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
ISL9012IRJRZ (No longer available, recommended replacement: ISL9000AIRJNZ-T)	DAAG	2.8	2.6	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
ISL9012IRJCZ (No longer available, recommended replacement: SL9000AIRJBZ-T)	DAAF	2.8	1.8	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
ISL9012IRFDZ	DCBK	2.5	2.0	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
ISL9012IRFCZ	DCBL	2.5	2.0	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
SL9012IRCJZ	DCBN	1.8	2.8	-40 to +85	10 Ld 3x3 DFN	L10.3x3C
SL9012IRCCZ	DCBP	1.8	1.8	-40 to +85	10 Ld 3x3 DFN	L10.3x3C

NOTES:

- 1. Add "-T" suffix for tape and reel. Please refer to TB347 for details on reel specifications.
- 2. For other output voltages, contact Intersil Marketing.
- 3. These Intersil Pb-free plastic packaged products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate PLUS ANNEAL - e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

Absolute Maximum Ratings

Supply Voltage (VIN)	7.1V
V _{O1.} V _{O2} Pin	3.6V
All Other Pins -0.3 to (VINI + 0	3)V

Recommended Operating Conditions

Ambient Temperature Range (T _A)	40°C to +85°C
Supply Voltage (VIN)	

Thermal Information

Thermal Resistance (Notes 4, 5)	θ_{JA} (°C/W)	θ_{JC} (°C/W)
3x3 DFN Package	50	10
Junction Temperature Range	40°	°C to +125°C
Operating Temperature Range	40	0°C to +85°C
Storage Temperature Range	65°	°C to +150°C
Pb-free Reflow Profile		ee link below
http://www.intersil.com/pbfree/Pb-FreeF	Reflow.asp	

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

NOTES:

- 4. θ_{JA} is measured in free air with the component mounted on a high effective thermal conductivity test board with "direct attach" features. See Tech Brief TB379.
- 5. θ_{JC} , "case temperature" location is at the center of the exposed metal pad on the package underside. See Tech Brief TB379.

Electrical Specifications

Unless otherwise noted, all parameters are guaranteed over the operational supply voltage and temperature range of the device as follows:

 T_A = -40°C to +85°C; V_{IN} = (V_O + 0.5V) to 6.5V with a minimum V_{IN} of 2.3V; C_{IN} = 1µF; C_O = 1µF; C_{BYP} = 0.01µF; C_{POR} = 0.01µF

PARAMETER	SYMBOL	TEST CONDITIONS	MIN (Note 8)	TYP	MAX (Note 8)	UNITS
DC CHARACTERISTICS	'				'	
Supply Voltage	V _{IN}		2.3		6.5	V
Ground Current		Quiescent condition: I _{O1} = 0μA; I _{O2} = 0μA				
	I _{DD1}	One LDO active		25	40	μΑ
	I _{DD2}	Both LDO active		45	60	μA
Shutdown Current	I _{DDS}	@+25°C		0.1	1.0	μA
UVLO Threshold	V _{UV+}		1.9	2.1	2.3	V
	V _{UV-}		1.6	1.8	2.0	V
Regulation Voltage Accuracy		Variation from nominal voltage output, $V_{IN} = V_O + 0.5$ to 5.5V, $T_J = -40$ °C to +125°C	-1.8		+1.8	%
Line Regulation		V _{IN} = (V _{OUT} + 1.0V relative to highest output voltage) to 5.5V	-0.2	0	0.2	%/V
Load Regulation		I _{OUT} = 100μA to 150mA (VO1 and VO2)		0.1	0.7	%
		I _{OUT} = 100μA to 300mA (VO2)			1.0	%
Maximum Output Current	I _{MAX}	VO1: Continuous	150			mA
		VO2: Continuous	300			mA
Internal Current Limit	I _{LIM}		350	475	600	mA
Dropout Voltage (Note 7)	V _{DO1}	I _O = 150mA; V _O > 2.1V (VO1)		125	200	mV
	V _{DO2}	I _O = 300mA; V _O < 2.5V (VO2)		300	500	mV
	V _{DO3}	$I_O = 300 \text{mA}; 2.5 \text{V} \le \text{V}_O \le 2.8 \text{V} \text{ (VO2)}$		250	400	mV
	V _{DO4}	I _O = 300mA; V _O > 2.8V (VO2)		200	325	mV
Thermal Shutdown Temperature	T _{SD+}			145		°C
	T _{SD-}			110		°C
AC CHARACTERISTICS						,
Ripple Rejection		I_{O} = 10mA, V_{IN} = 2.8V(min), V_{O} = 1.8V, C_{BYP} = 0.1 μ F				
		@ 1kHz		70		dB
		@ 10kHz		55		dB
		@ 100kHz		40		dB

Electrical Specifications

Unless otherwise noted, all parameters are guaranteed over the operational supply voltage and temperature range of the device as follows:

 $T_A = -40$ °C to +85°C; $V_{IN} = (V_O + 0.5V)$ to 6.5V with a minimum V_{IN} of 2.3V; $C_{IN} = 1\mu F$; $C_O = 1\mu F$; $C_{BYP} = 0.01\mu F$; $C_{POR} = 0.01\mu F$ (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN (Note 8)	TYP	MAX (Note 8)	UNITS
Output Noise Voltage		I_O = 100 μ A, V_O = 1.5V, T_A = +25°C, C_{BYP} = 0.1 μ F BW = 10Hz to 100kHz (Note 6)		30		μVrms
DEVICE START-UP CHARACTE	RISTICS					
Device Enable TIme	t _{EN}	Time from assertion of the ENx pin to when the output voltage reaches 95% of the VO(nom)		250	500	μs
LDO Soft-start Ramp Rate	tssR	Slope of linear portion of LDO output voltage ramp during start-up		30	60	μs/V
EN1, EN2 PIN CHARACTERIST	ics					
Input Low Voltage	V _{IL}		-0.3		0.5	V
Input High Voltage	V _{IH}		1.4		V _{IN} +0.3	V
Input Leakage Current	I _{IL} , I _{IH}				0.1	μA
Pin Capacitance	C _{PIN}	Informative		5		pF
POR PIN CHARACTERISTICS						
POR Thresholds	V _{POR+}	As a percentage of nominal output voltage	91	94	97	%
	V _{POR-}		87	90	93	%
POR Delay	t _{PLH}	CPOR = 0.01µF	100	200	300	ms
	t _{PHL}			25		μs
POR Pin Output Low Voltage	V _{OL}	@I _{OL} = 1.0mA			0.2	V
POR Pin Internal Pull-Up Resistance	R _{POR}		78	100	180	kΩ

NOTES:

- 6. Limits established by characterization and are not production tested.
- 7. VOx = 0.98*VOx(NOM); Valid for VOx greater than 1.85V.
- 8. Parts are 100% tested at +25°C. Temperature limits established by characterization and are not production tested.

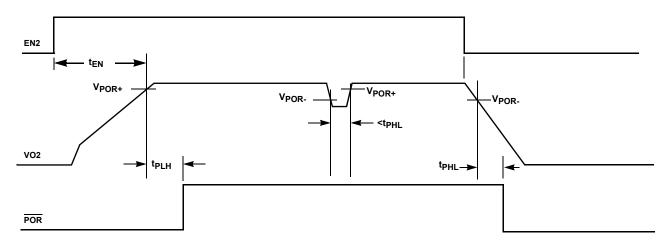


FIGURE 1. TIMING PARAMETER DEFINITION

Typical Performance Curves

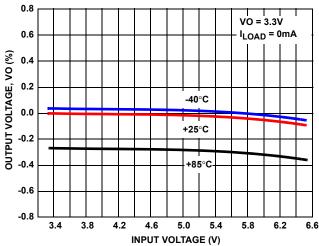


FIGURE 2. OUTPUT VOLTAGE vs INPUT VOLTAGE (3.3V OUTPUT)

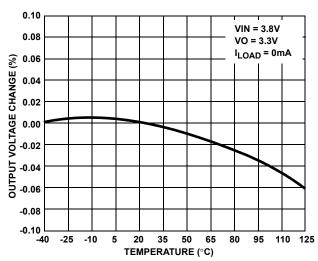


FIGURE 4. OUTPUT VOLTAGE CHANGE vs TEMPERATURE

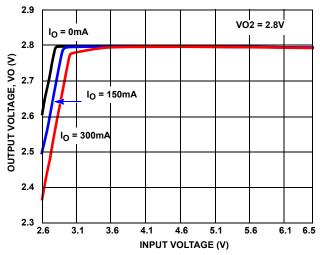


FIGURE 6. OUTPUT VOLTAGE vs INPUT VOLTAGE (VO2 = 2.8V)

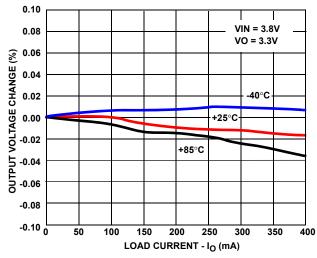


FIGURE 3. OUTPUT VOLTAGE CHANGE vs LOAD CURRENT

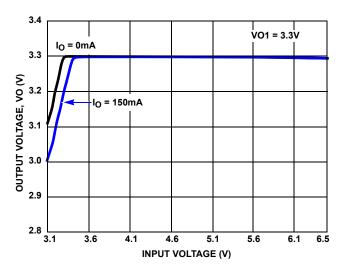


FIGURE 5. OUTPUT VOLTAGE vs INPUT VOLTAGE (VO1 = 3.3V)

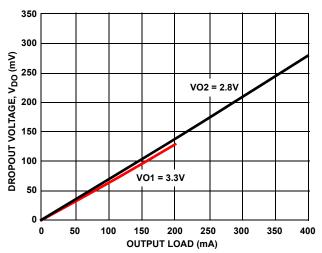


FIGURE 7. VO1 DROPOUT VOLTAGE vs LOAD CURRENT

Typical Performance Curves (Continued)

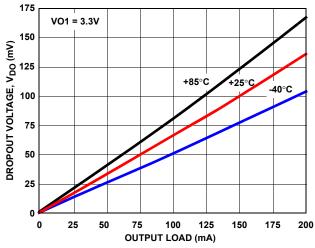


FIGURE 8. VO1 DROPOUT VOLTAGE vs LOAD CURRENT

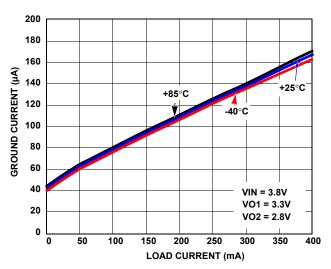


FIGURE 10. GROUND CURRENT vs LOAD

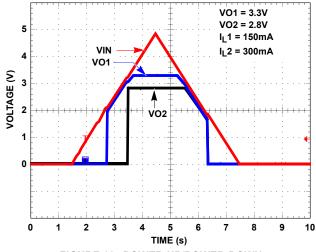


FIGURE 12. POWER-UP/POWER-DOWN

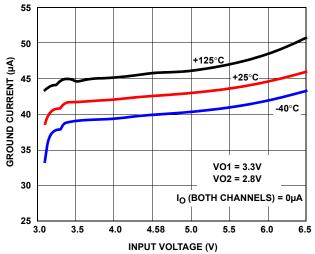


FIGURE 9. GROUND CURRENT vs INPUT VOLTAGE

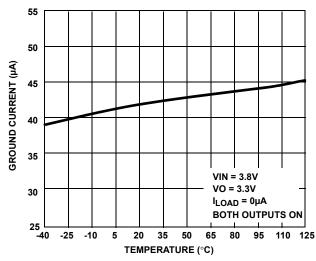


FIGURE 11. GROUND CURRENT vs TEMPERATURE

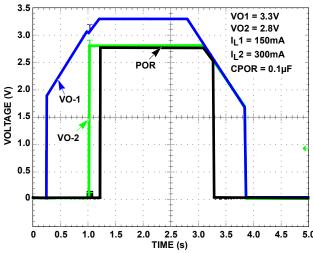


FIGURE 13. POWER-UP/POWER-DOWN WITH POR SIGNALS

Typical Performance Curves (Continued)

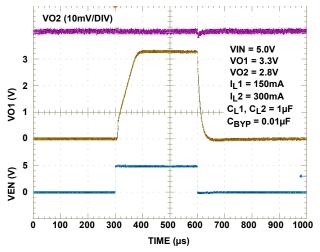


FIGURE 14. TURN ON/TURN OFF RESPONSE

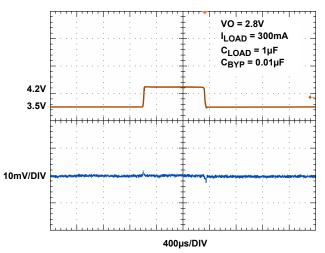


FIGURE 16. LINE TRANSIENT RESPONSE, 2.8V OUTPUT

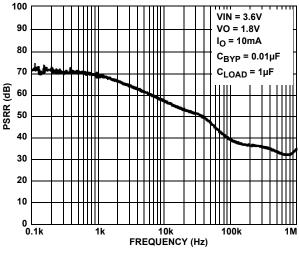


FIGURE 18. PSRR vs FREQUENCY

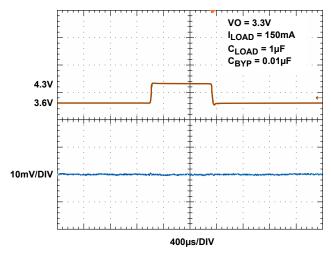


FIGURE 15. LINE TRANSIENT RESPONSE, 3.3V OUTPUT

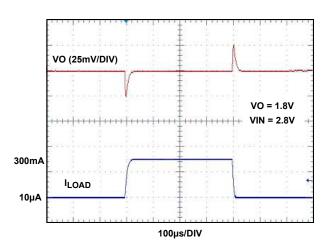


FIGURE 17. LOAD TRANSIENT RESPONSE

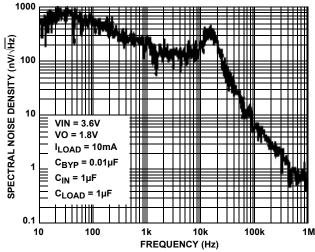
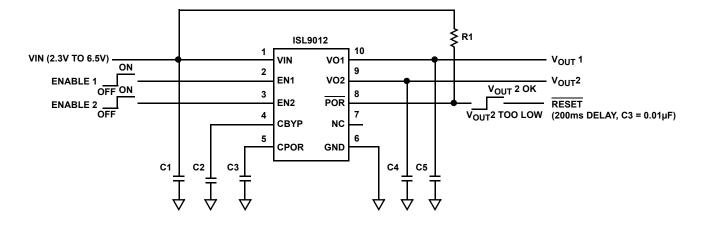


FIGURE 19. SPECTRAL NOISE DENSITY vs FREQUENCY

Pin Description

PIN NUMBER	PIN NAME	TYPE	DESCRIPTION
1	VIN	Analog I/O	Supply Voltage/LDO Input: Connect a 1µF capacitor to GND.
2	EN1	Low Voltage Compatible CMOS Input	LDO-1 Enable.
3	EN2	Low Voltage Compatible CMOS Input	LDO-2 Enable.
4	CBYP	Analog I/O	Reference Bypass Capacitor Pin: Optionally connect capacitor of value $0.01\mu F$ to $1\mu F$ between this pin and GND to tune in the desired noise and PSRR performance.
5	CPOR	Analog I/O	POR Delay Setting Capacitor Pin: Connect a capacitor between this pin and GND to delay the POR output release after LDO-2 output reaches 94% of its specified voltage level (200ms delay per 0.01µF).
6	GND	Ground	GND is the connection to system ground. Connect to PCB Ground plane.
7	NC	NC	No Connection.
8	POR	Open Drain Output (1mA)	Open-drain POR Output for LDO-2 (active-low).
9	VO2	Analog I/O	LDO-2 Output: Connect capacitor of value 1µF to 10µF to GND (1µF recommended).
10	VO1	Analog I/O	LDO-1 Output: Connect capacitor of value 1µF to 10µF to GND (1µF recommended).

Typical Application



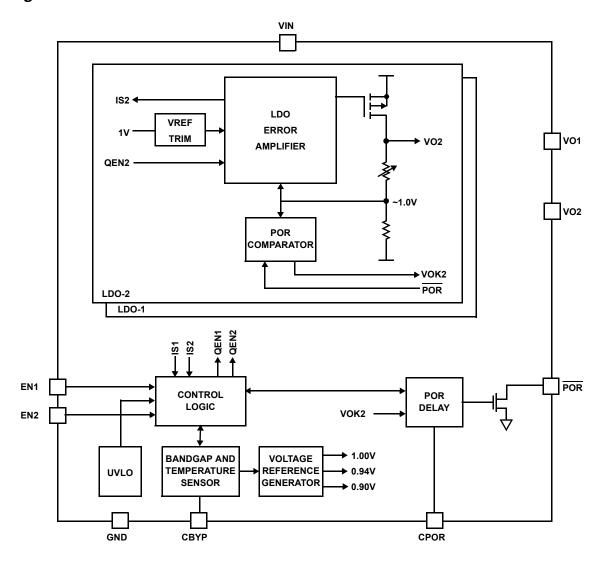
C1, C4, C5: 1µF X5R CERAMIC CAPACITOR

C2: $0.01\mu F$ X5R CERAMIC CAPACITOR

 $\textbf{C3: } \textbf{0.01} \mu \textbf{F X5R CERAMIC CAPACITOR}$

R1: 100k Ω RESISTOR, 5%

Block Diagram



Functional Description

The ISL9012 contains all circuitry required to implement two high performance LDO's. High performance is achieved through a circuit that delivers fast transient response to varying load conditions. In a quiescent condition, the ISL9012 adjusts its biasing to achieve the lowest standby current consumption.

The device also integrates current limit protection, smart thermal shutdown protection, staged turn-on and soft-start. Smart Thermal shutdown protects the device against overheating. Staged turn-on and soft-start minimize start-up input current surges without causing excessive device turn-on time.

Power Control

The ISL9012 has two separate enable pins, EN1 and EN2, to individually control power to each of the LDO outputs. When both EN1 and EN2 are low, the device is in shutdown

mode. During this condition, all on-chip circuits are off, and the device draws minimum current, typically less than $0.1\mu A$. When one or both of the enable pins are asserted, the device first polls the output of the UVLO detector to ensure that VIN voltage is at least about 2.1V. Once verified, the device initiates a start-up sequence. During the start-up sequence, trim settings are first read and latched. Then, sequentially, the bandgap, reference voltage and current generation circuitry power up. Once the references are stable, a fast-start circuit quickly charges the external reference bypass capacitor (connected to the CBYP pin) to the proper operating voltage. After the bypass capacitor has been charged, the LDO's power up.

If EN1 is brought high, and EN2 goes high before the VO1 output stabilizes, the ISL9012 delays the VO2 turn-on until the VO1 output reaches its target level.

If EN2 is brought high, and EN1 goes high before VO2 starts its output ramp, then VO1 turns on first and the ISL9012

delays the VO2 turn-on until the VO1 output reaches its target level.

If EN2 is brought high, and EN1 goes high after VO2 starts its output ramp, then the ISL9012 immediately starts to ramp up the VO1 output.

If both EN1 and EN2 are high, the VO1 output has priority, and is always powered up first.

During operation, whenever the VIN voltage drops below about 1.8V, the ISL9012 immediately disables both LDO outputs. When VIN rises back above 2.1V, the device re-initiates its start-up sequence and LDO operation will resume automatically.

Reference Generation

The reference generation circuitry includes a trimmed bandgap, a trimmed voltage reference divider, a trimmed current reference generator, and an RC noise filter. The filter includes the external capacitor connected to the CBYP pin. A 0.01µF capacitor connected CBYP implements a 100Hz lowpass filter, and is recommended for most high performance applications. For the lowest noise application, a 0.1µF or greater CBYP capacitor should be used. This filters the reference noise to below the 10Hz to1kHz frequency band, which is crucial in many noise-sensitive applications.

The bandgap generates a zero temperature coefficient (TC) voltage for the reference divider. The reference divider provides the regulation reference, POR detection thresholds, and other voltage references required for current generation and over-temperature detection.

The current generator outputs references required for adaptive biasing as well as references for LDO output current limit and thermal shutdown determination.

LDO Regulation and Programmable Output Divider

The LDO Regulator is implemented with a high-gain operational amplifier driving a PMOS pass transistor. The design of the ISL9012 provides a regulator that has low quiescent current, fast transient response, and overall stability across all operating and load current conditions. LDO stability is guaranteed for a 1µF to 10µF output capacitor that has a tolerance better than 20% and ESR less than $200m\Omega$. The design is performance-optimized for a $1\mu F$ capacitor. Unless limited by the application, use of an output capacitor value above 4.7µF is not recommended as LDO performance improvement is minimal.

Soft-start circuitry integrated into each LDO limits the initial ramp-up rate to about 30µs/V to minimize current surge. The ISL9012 provides short-circuit protection by limiting the output current to about 475mA.

Each LDO uses an independently trimmed 1V reference. An internal resistor divider drops the LDO output voltage down to 1V. This is compared to the 1V reference for regulation. The resistor division ratio is programmed in the factory to

one of the following output voltages: 1.5V, 1.8V, 1.85V, 2.5V, 2.6V, 2.7V, 2.8V, 2.85V, 2.9V, 3.0V, and 3.3V.

Power-On Reset Generation

LDO-2 has a Power-on Reset signal generation circuit which outputs to the POR pin. The POR signal is generated as follows:

A POR comparator continuously monitors the voltage of the LDO-2 output. The LDO enters a power-good state when the output voltage is above 94% of the expected output voltage for a period exceeding the LDO PGOOD entry delay time. In the power-good state, the open-drain POR output is in a high-impedance state. An external resistor can be added between the POR output and either LDO output or the input voltage, VIN.

The power-good state is exited when the LDO-2 output falls below 90% of the expected output voltage for a period longer than the PGOOD exit delay time. While power-good is false, the ISL9012 pulls the respective POR pin low.

The PGOOD entry and exit delays are determined by the value of the external capacitor connected to the CPOR pin. For a 0.01µF capacitor, the entry and exit delays are 200ms and 25µs respectively. Larger or smaller capacitor values will yield proportionately longer or shorter delay times. The POR exit delay should never be allowed to be less than 10µs to ensure sufficient immunity against transient induced false POR triggering.

Overheat Detection

The bandgap outputs a proportional-to-temperature current that is indicative of the temperature of the silicon. This current is compared with references to determine if the device is in danger of damage due to overheating. When the die temperature reaches about +145°C, one or both of the LDO's momentarily shut down until the die cools sufficiently. In the overheat condition, only the LDO sourcing more than 50mA will be shut off. This does not affect the operation of the other LDO. If both LDOs source more than 50mA and an overheat condition occurs, both LDO outputs are disabled. Once the die temperature falls back below about +110°C. the disabled LDO(s) are re-enabled and soft-start automatically takes place.

Revision History

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to the web to make sure that you have the latest revision.

DATE	REVISION	CHANGE
December 10, 2015	FN9220.4	Added Rev History beginning with Rev 4. Added About Intersil. Verbiage. Updated Ordering Information table on page 2 Updated POD L10.3x3C to most current version. Revision changes are as follows: Updated Format to new standard Removed package outline and included center to center distance between lands on recommended land pattern. Removed Note 4 "Dimension b applies to the metallized terminal and is measured between 0.18mm and 0.30mm from the terminal tip." since it is not applicable to this package. Renumbered notes accordingly. Tiebar Note 4 updated From: Tiebar shown (if present) is a non-functional feature. To: Tiebar shown (if present) is a non-functional feature and may be located on any of the 4 sides (or ends).

About Intersil

Intersil Corporation is a leading provider of innovative power management and precision analog solutions. The company's products address some of the largest markets within the industrial and infrastructure, mobile computing and high-end consumer markets.

For the most updated datasheet, application notes, related documentation and related parts, please see the respective product information page found at www.intersil.com.

You may report errors or suggestions for improving this datasheet by visiting www.intersil.com/ask.

Reliability reports are also available from our website at www.intersil.com/support

All Intersil U.S. products are manufactured, assembled and tested utilizing ISO9001 quality systems. Intersil Corporation's quality certifications can be viewed at www.intersil.com/design/quality

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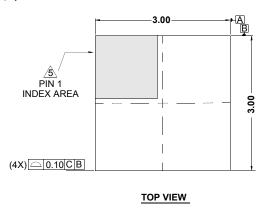
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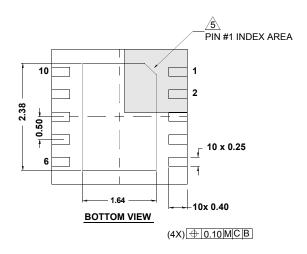
intersil

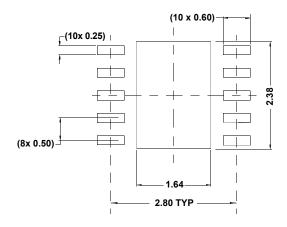
Package Outline Drawing

L10.3x3C

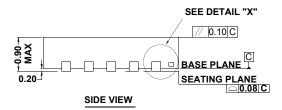
10 LEAD DUAL FLAT PACKAGE (DFN) Rev 4, 3/15

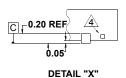






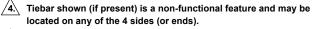
TYPICAL RECOMMENDED LAND PATTERN





NOTES:

- Dimensions are in millimeters.
 Dimensions in () for Reference Only.
- 2. Dimensioning and tolerancing conform to AMSE Y14.5m-1994.
- 3. Unless otherwise specified, tolerance : Decimal ± 0.05



√5. The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.

6. Compliant to JEDEC MO-229-WEED-3 except for E-PAD dimensions.